

FE for time measurements

N. Seguin-Moreau on behalf of OMEGA

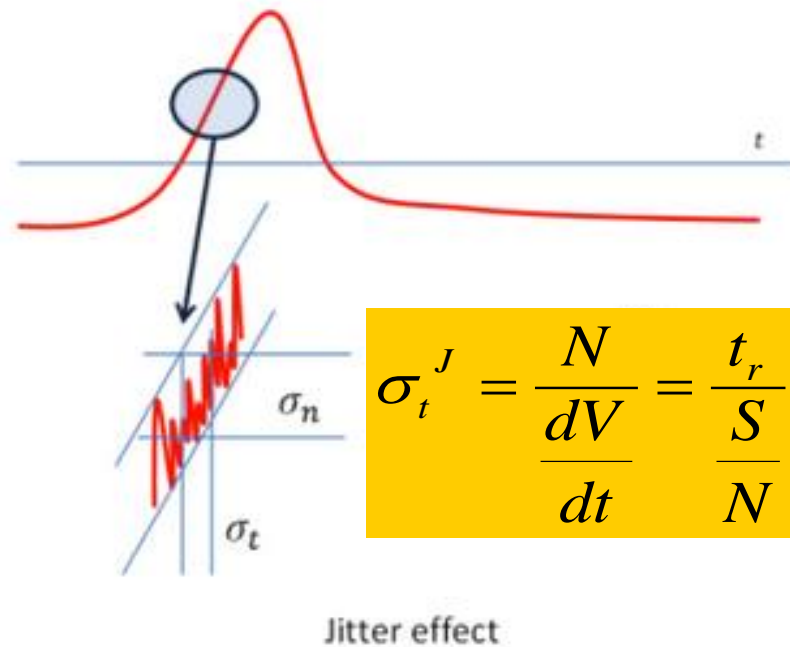
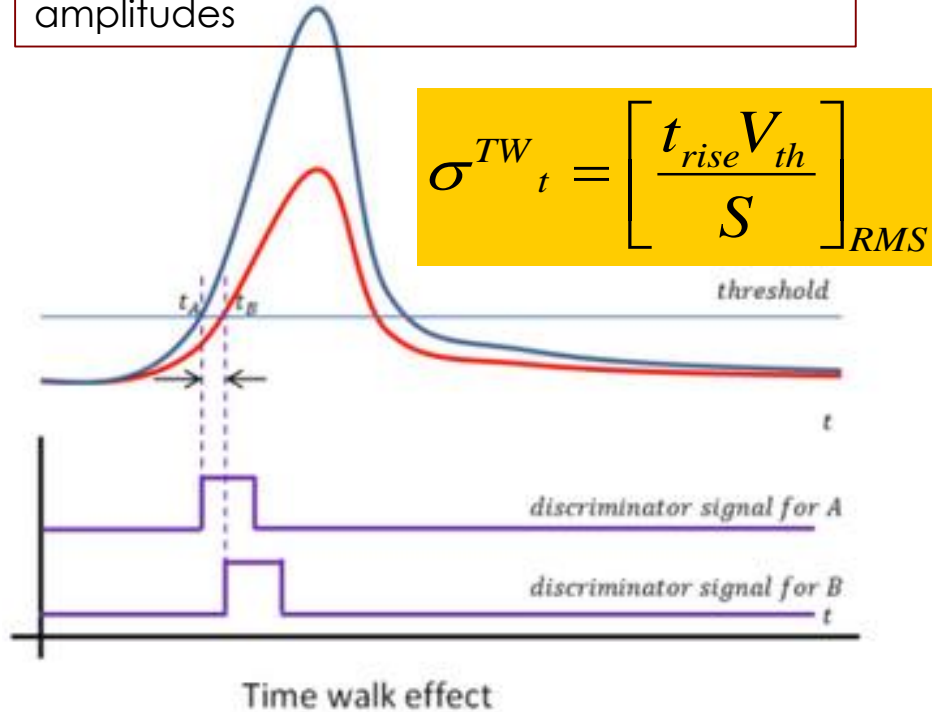
- Time resolution $< 50\text{ps}$ required by many experiments/applications keeping low power, large dynamic range
- **PET/ Time of Flight** measurements (SiPM)
 - Dynamic range : 1 pe (100fC) up to 3000 pe (300 pC)
 - Time resolution $< 100\text{ps}$
- **CMS High Granularity CALorimeter:** (Si pin diodes)
 - **Dynamic range** EM showers: few fC up to ~ 10 pC (2500-5000 mips)
 - Calorimetry \Rightarrow **Precision /linearity** $< 1\%$
 - **Fast timing ability** (50ps) for > 10 mips desirable
 - **Peaking time** 15-20 ns (minimize noise, minimise Out of Time pileup)
 - **Power on detector** $< \sim 10$ mW/channel all included (except power loss in cables/converters and power dissipated by sensors after irradiation).
- **ATLAS High Granularity Timing Detector** (LGAD or Si Pin diodes)
 - Time performance < 50 ps : To reject Time Pile up events \Rightarrow better particle identification
 - Dynamic range: up to few Mips or 200Mips (depending on Preshower)



Time walk and Time jitter

Time walk: the voltage value V_0 is reached at different time for signal of different amplitudes

Jitter: the noise is summed to the signal, causing amplitude variations



Due to the physics of signal formation

Mostly due to electronic noise

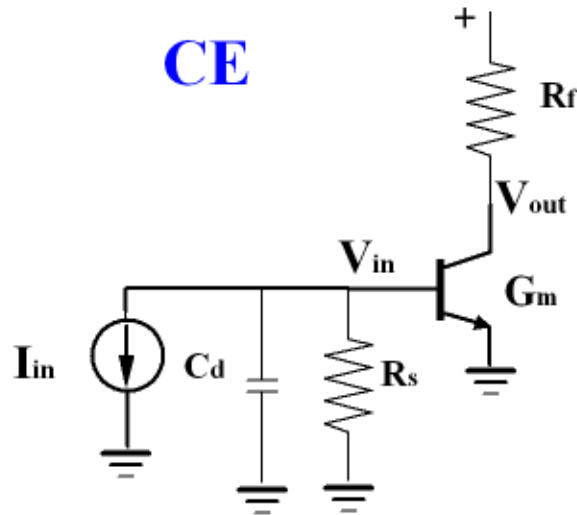
$$\sigma_t^2 = \left(\frac{t_{rise}}{S/N} \right)^2 + \left(\left[\frac{t_{rise} V_{th}}{S} \right]_{RMS} \right)^2 + \left(\frac{TDC_{bin}}{\sqrt{12}} \right)^2 + (Landau Shape)^2$$

Jitter

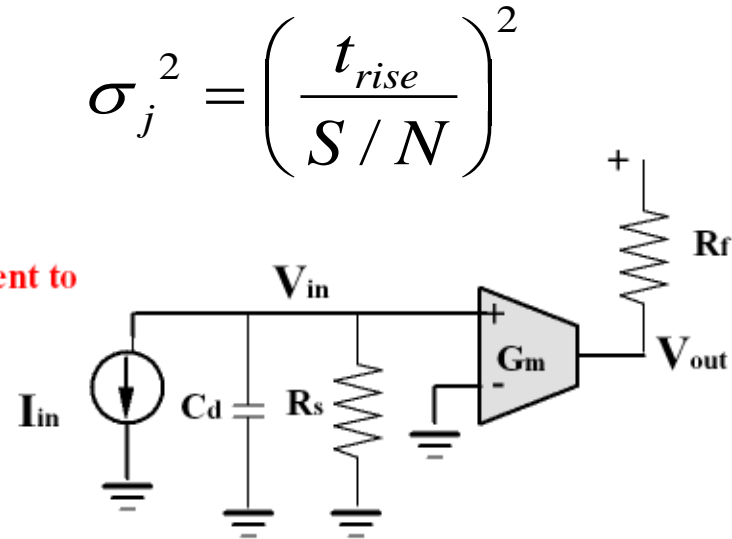
Time Walk

TDC

CE

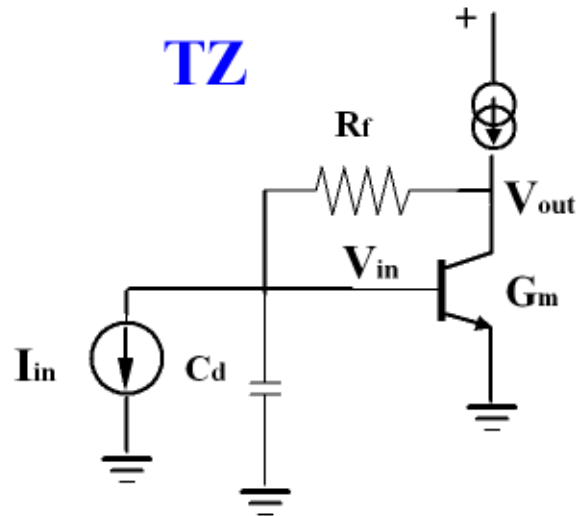


equivalent to
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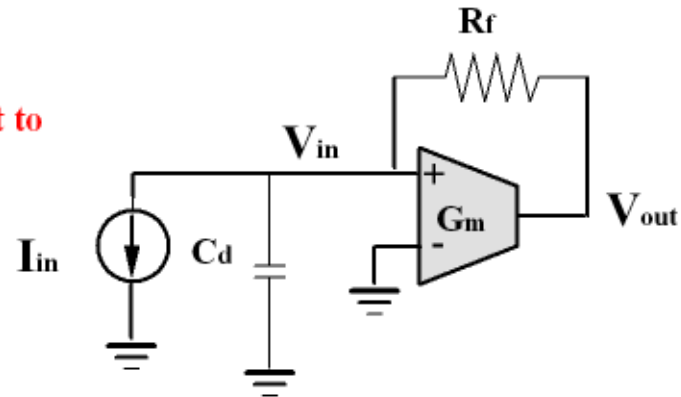


$$\sigma_j^2 = \left(\frac{t_{rise}}{S/N} \right)^2$$

TZ

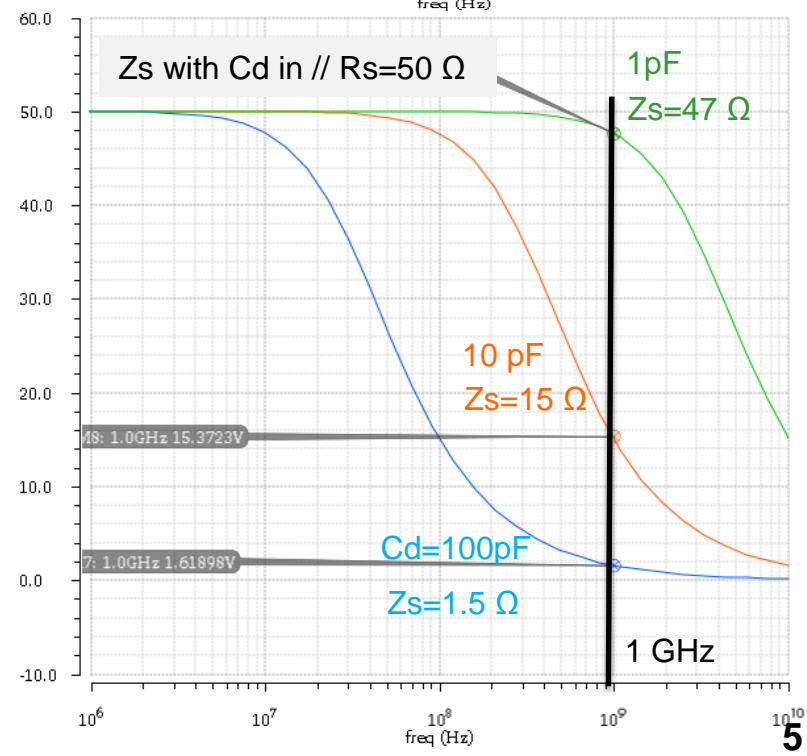
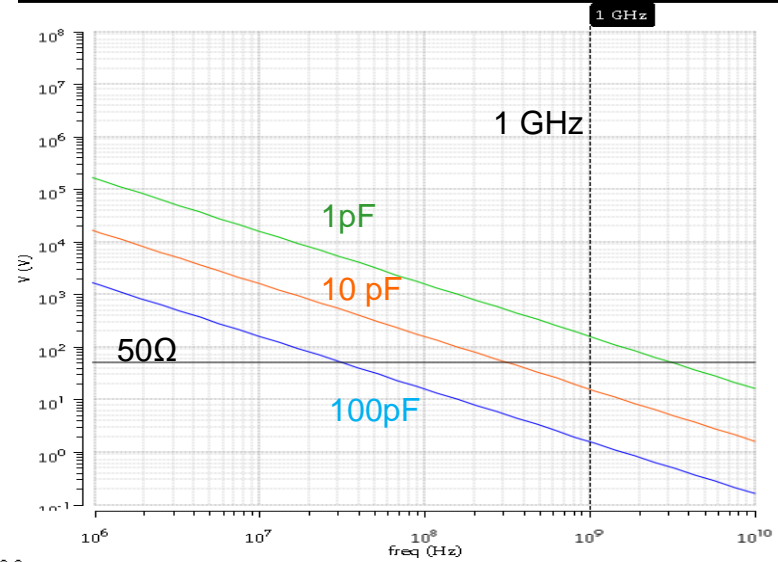
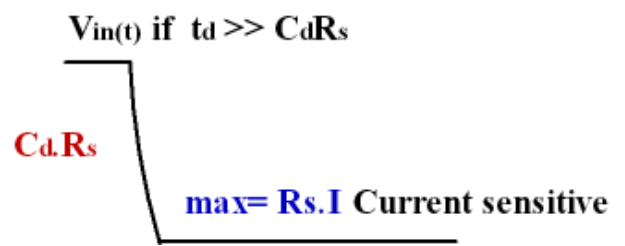
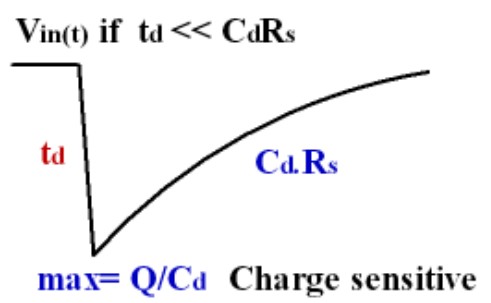
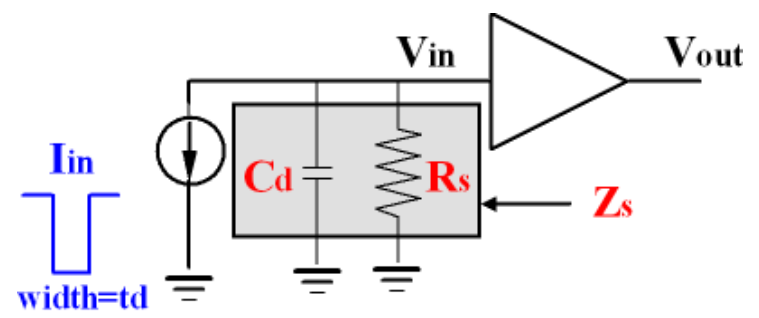


equivalent to
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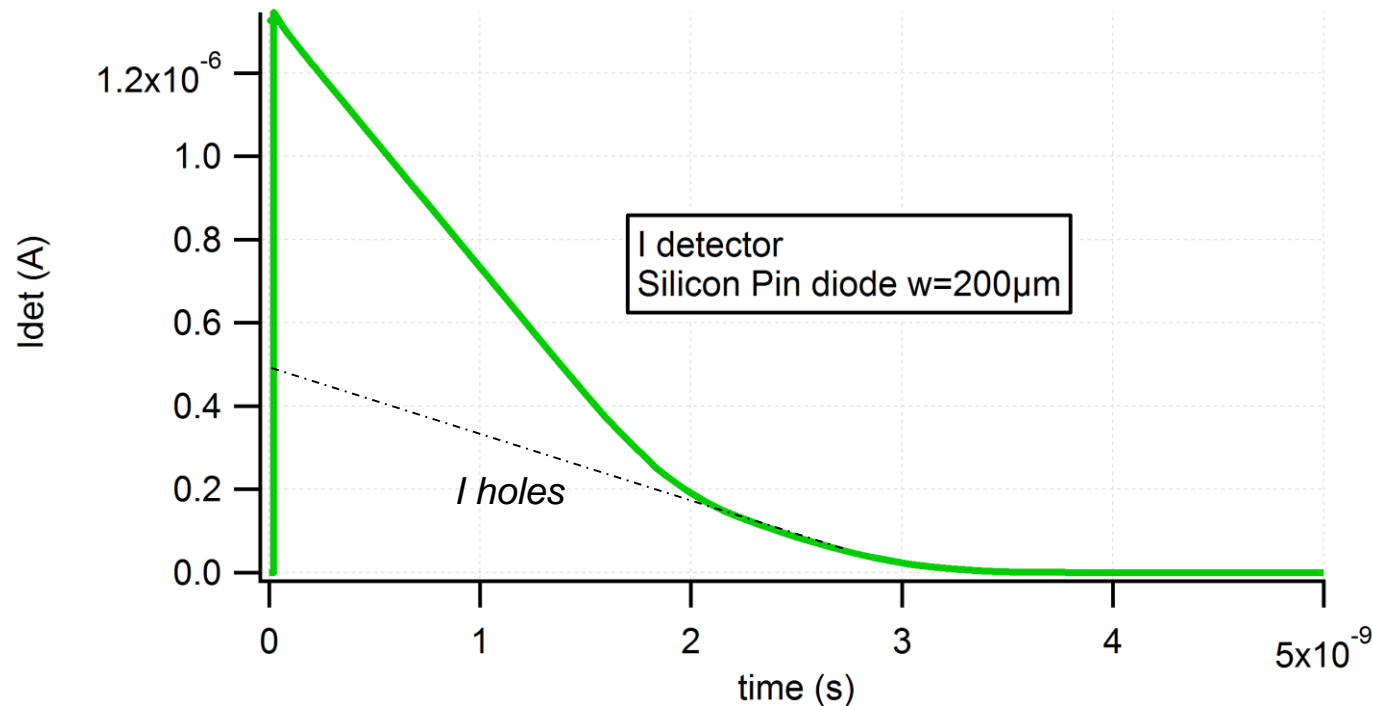


Vin @1 GHz

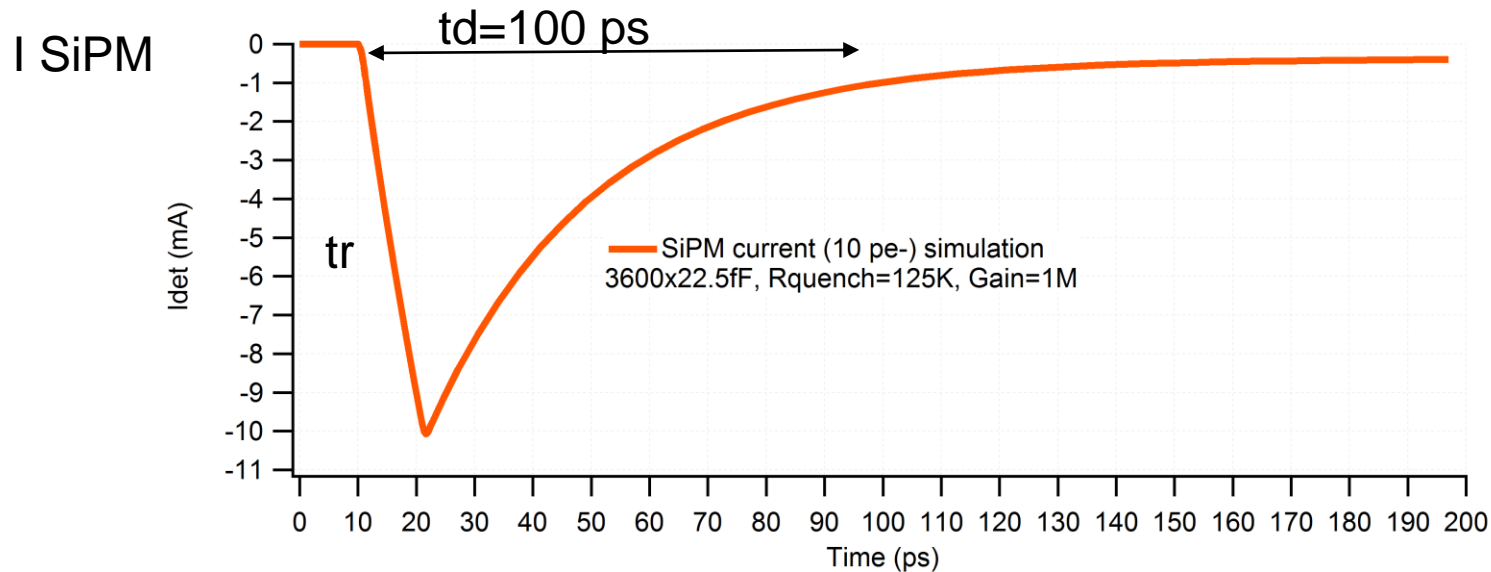
- 1 GHz, Cd=few tenths of pF, width of the input signal <1ns
- Cd>10 pF, Zs@1GHz dominated by Cd
- Rise time: tr= td when td<<CdRs and tr=CdRs when td>>CdRs



- Simulation of a Si Pin diode detector: $w = 200\mu\text{m}$
- t_r is very short but the drift time is quite « long »: $t_d = 3\text{ ns}$



- Simulation of a SiPM detector (10pe-)
 - 3600x22.5fF (80 pF), Gain=1M, Rquench=125K, Cquench=5fF, CL=10pF
- tr is very short (10 ps), td very short (100ps),
- Cd=80pF, Rin=50Ω => td << RinCd => Preamp rise time must be minimized (Fast preamp in Petiroc: tr_amplifier 10-90% =300ps)



CE and TZ : Vout (= S) at High Frequency and Cd>10pF

$$\sigma_t^J = \frac{N}{dV} = \frac{t_r}{S}$$

Cd > 10 pF, Zs @ 1GHz dominated by Cd

• CE using an OTA with gain Gm

- $V_{OUT} = -G_m (Z_F // Z_L) V_{IN}$

With ZL neglected and Zs=Cd and ZF=RF

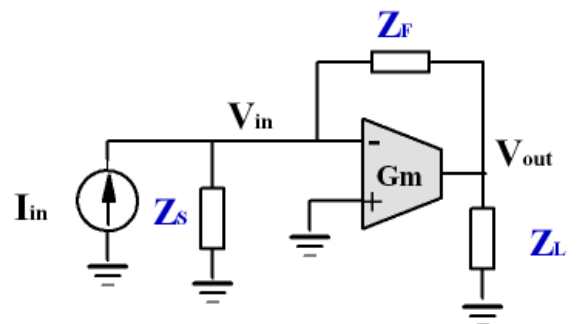
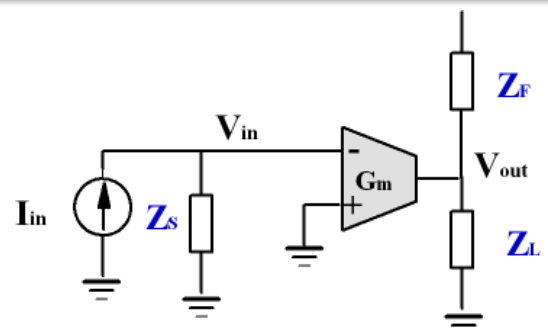
- $V_{IN} = Z_S I_{IN} = \frac{1}{j\omega C_d} I_{IN}$
- $V_{OUT} = -G_m Z_F V_{IN} = -\frac{G_m Z_F}{j\omega C_d} I_{IN}$
- $V_{OUT} = -G_m R_F \frac{Q_{IN}}{C_d}$
- $Z_{IN} = Z_S \Rightarrow C_d$
- $Z_{OUT} = Z_F = R_F$

• TZ using an OTA with gain Gm

- $I_{OUT} = V_{OUT} / Z_L + (V_{OUT} - V_{IN}) / Z_F$
- $I_{IN} = V_{IN} / Z_S - (V_{OUT} - V_{IN}) / Z_F$
- $I_{OUT} = -G_m V_{IN}$

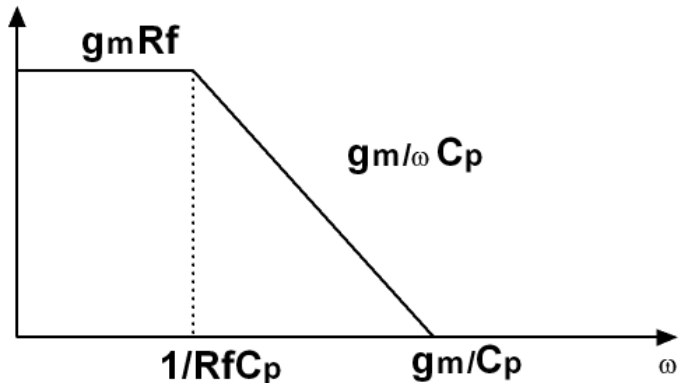
With ZL neglected and Zs=Cd and ZF=RF

- $I_{IN} = \frac{V_{in}}{Z_s} - I_{OUT}$
- $V_{IN} = \frac{I_{IN}}{(\frac{1}{Z_s} + G_m)} = \frac{1}{1 + j\omega \frac{C_d}{G_m}} I_{IN}$
- $V_{OUT} = (1 - G_m Z_F) V_{IN}$
- $V_{OUT} = \frac{1 - G_m R_F}{1 + j\omega \frac{C_d}{G_m}} I_{IN} \approx -G_m R_F \frac{I_{IN}}{j\omega C_d} = -G_m R_F \frac{Q_{IN}}{C_d}$
- $Z_{IN} = \frac{1}{1 + j\omega \frac{C_d}{G_m}} \Rightarrow 1 / G_m \text{ in // with } C_d$
- $Z_{OUT} = \frac{R_F}{1 + G_m R_F} \sim \frac{1}{G_m}$

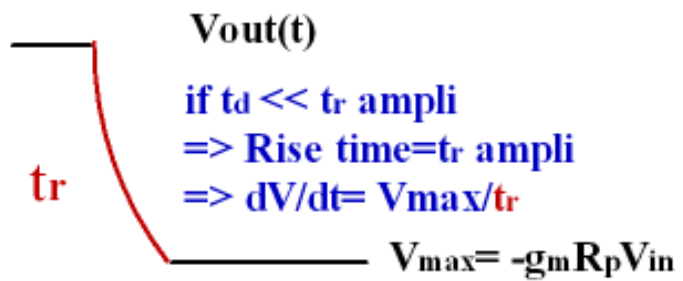
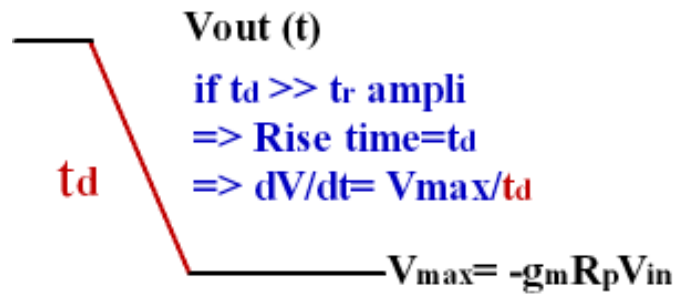
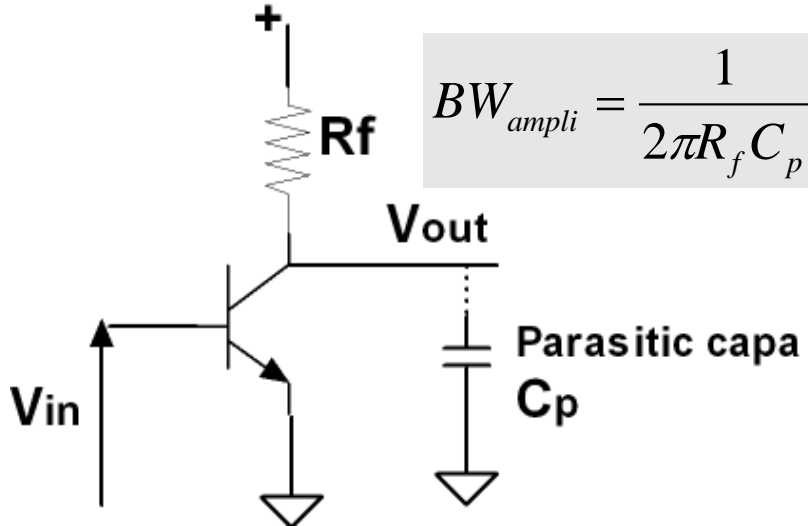


$$V_{out}(s) = -g_m (R_f // C_p) V_{in}(s)$$

$$\frac{V_{out}(\omega)}{V_{in}(\omega)} = -g_m \frac{R_f}{j\omega C_p \left(R_f + \frac{1}{j\omega C_p} \right)} = \frac{-g_m R_f}{j\omega C_p R_f + 1}$$



$$BW_{ampli} = \frac{1}{2\pi R_f C_p} = \frac{0.35}{t_{r_ampli}}$$



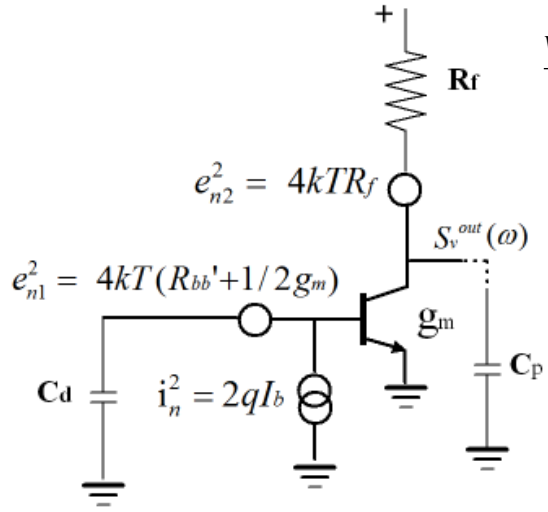
$$\sigma_t^J = \frac{N}{\frac{dV}{dt}} = \frac{t_r}{S} \frac{N}{N}$$

$$\frac{dV}{dt} \approx \frac{V_{max}}{\sqrt{t_{r_ampli}^2 + t_d^2}}$$

NOISE TZ and CE (N)

$$\sigma_t^J = \frac{N}{dV} = \frac{t_r}{S}$$

Omega



$$\frac{V_{out}(\omega)}{V_{in}(\omega)} = \frac{-g_m R_f}{j\omega R_f C_p + 1}$$

$$S_{v \text{ Bipolar}}^{out}(\omega) = (g_m R_f)^2 \left(4kTR_{bb'} + \frac{4kT}{2g_m} \right) + 4kTR_f$$

$$S_{v \text{ MOS}}^{out}(\omega) = (g_m R_f)^2 \left(4kTR_{GG'} + \frac{4kT\Gamma}{g_m} \right) + 4kTR_f + k \frac{I_D}{f}$$

- Similar noise for CE and TZ
- Parallel noise ($2qI_b$ or $2qI_G$) negligible at HF
- rms noise v_n depends on the \sqrt{BW}
- Noise is independent of C_d
- But the signal is not independent of C_d
- S/N depends of C_d and BW

$$v_n^2 = \int S_v(\omega) |H(\omega)|^2 \frac{d\omega}{2\pi}$$

$$v_n^2 = \int S_v(\omega) \frac{(g_m R_f)^2}{(1 + \omega^2 R_f^2 C_p^2)} \frac{d\omega}{2\pi}$$

$$N = v_n \approx R_f \sqrt{2kTg_m BW}$$

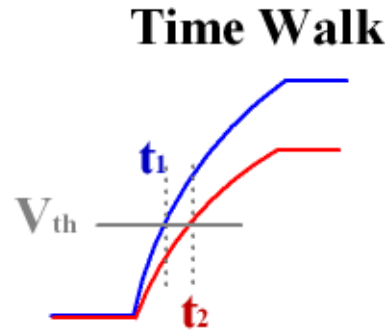
$$V_{OUT} = -g_m R_f \frac{Q_{IN}}{C_d}$$

$$\frac{S}{N} \approx \frac{\alpha \sqrt{g_m}}{C_d \sqrt{BW}} \approx \alpha \frac{\sqrt{g_m} \sqrt{t_r \text{ ampli}}}{C_d}$$

$$\sigma_t^J = \frac{N}{\frac{dV}{dt}} = \frac{N}{\frac{S}{\sqrt{t_{r-a}^2 + t_d^2}}} = \frac{N}{\frac{S}{N}} = \frac{\sqrt{t_{r-a}^2 + t_d^2}}{\frac{S}{N}} = \alpha \frac{\sqrt{t_{r-a}^2 + t_d^2}}{\sqrt{g_m} \frac{C_d}{\sqrt{t_{r-a}}}} = \alpha \frac{C_d}{\sqrt{g_m}} \frac{\sqrt{t_{r-a}^2 + t_d^2}}{\sqrt{t_{r-a}}}$$

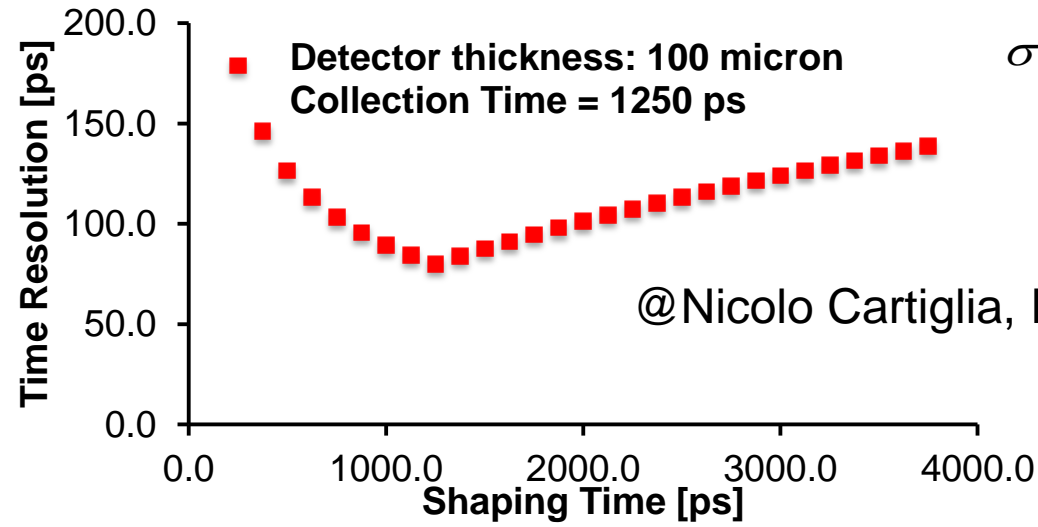
Optimum value: $t_{r-a} = t_d$

$$\sigma_t^J \approx \alpha C_d \sqrt{\frac{t_d}{g_m}}$$



$$\sigma_t^{TW} = \left[\frac{\sqrt{t_{r-a}^2 + t_d^2} V_{th}}{S} \right]_{RMS}$$

$$\sigma_t^J = \frac{\sigma_N}{\frac{dV}{dt}}$$



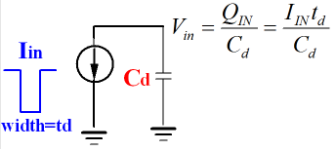
@Nicolo Cartiglia, INFN Torino

CE in TSMC 130 nm: jitter vs tr (BW) and td

- With I source trans (0 for 2 pF or 1.8mA for 20pF)
- Follower (connected to a discriminator)
- Normalization to 1 fC, square pulse.

$$\sigma_t^J = \frac{N}{\frac{dV}{dt}} = \frac{t_r}{\frac{S}{N}} = \frac{\sqrt{t_{r_ampli}^2 + t_d^2}}{\frac{S}{N}}$$

POWER: 0.5mW/ mm²

CE	Cd=2pF (Id=220 μA)	Cd=20pF (Id=2.1 mA)
<p>td=10ps Qin=lin.td= 100μA.10ps=1fC</p>  <p>$V_m = \frac{Q_{IN}}{C_d} = \frac{I_{IN} t_d}{C_d}$</p>	<p>out = 6.9 mV out_fol=6.1 mV tr_fol=284 ps BWa=1.2 GHz rms=0.485 mV S/N=12.6 σj=284ps/12.6=23 ps</p>	<p>out=3.37 mV out_fol=3.1 mV tr_fol=290 ps BWa=1.2 GHz rms=1.2 mV S/N=2.6 σj=290ps/2.6=110 ps</p>
<p>td=1ns and tr_ampli=td CL=100fF Qin= 1μA.1ns=1fC</p>	<p>out=6.4 mV out_fol=5.9 mV tr_fol=1.1ns BWa=410 MHz rms=0.39 mV S/N=15 σj=1.1ns/15=73 ps</p>	<p>out=3.2 mV out_fol=3.05 mV tr_fol=1.1 ns BWa=440 MHz rms=0.8mV S/N=3.8 σj=1.1ns/3.8=288 ps</p>

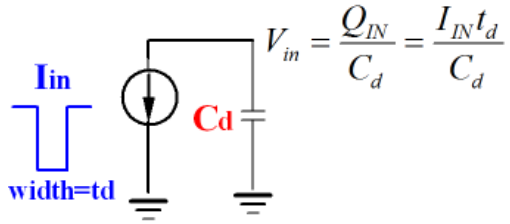
lin pulse td=1ns 1uA : WFMs with 2 and 20pF



Mon Apr 25 15:03:16 2016

Transient Response

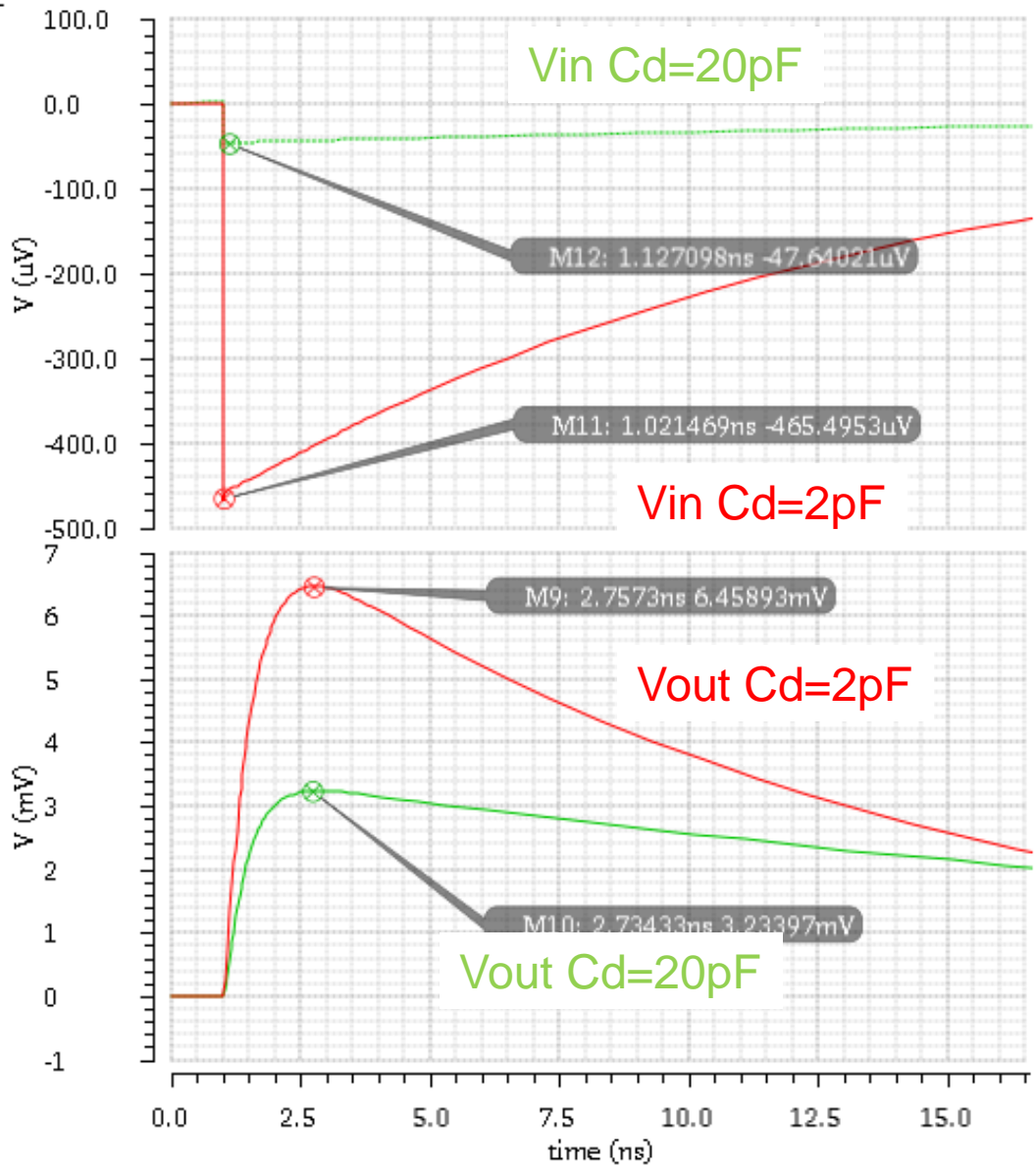
Name	Vis
Cd=20pF Vin=1fC/20pF	<input checked="" type="checkbox"/>
Cd=2pF Vin=1fC/2pF	<input checked="" type="checkbox"/>



Cd=20pF out	<input checked="" type="checkbox"/>
Cd=2pF out	<input checked="" type="checkbox"/>

20pF → 2pF:
 Signal=Qin/Cd x 10
 I/10 => √gm divided by √10
 => S/N x √10

$$\frac{S}{N} \approx \frac{\alpha \sqrt{g_m}}{C_d \sqrt{BW}} \approx \alpha \frac{\sqrt{g_m} \sqrt{t_{r_ampli}}}{C_d}$$



- Time of Flight read-out chip (**SiGe 0.35 μ m**) with embedded TAC (25 ps bin) and 10-bit ADC for Q and T digitization

- Front-end
 - **Common Emitter**, DC coupled to detector
 - **Fast discriminator**



- Variable shaping time shaper for charge measurement. Dynamic range: 160 fC up to 400 pC

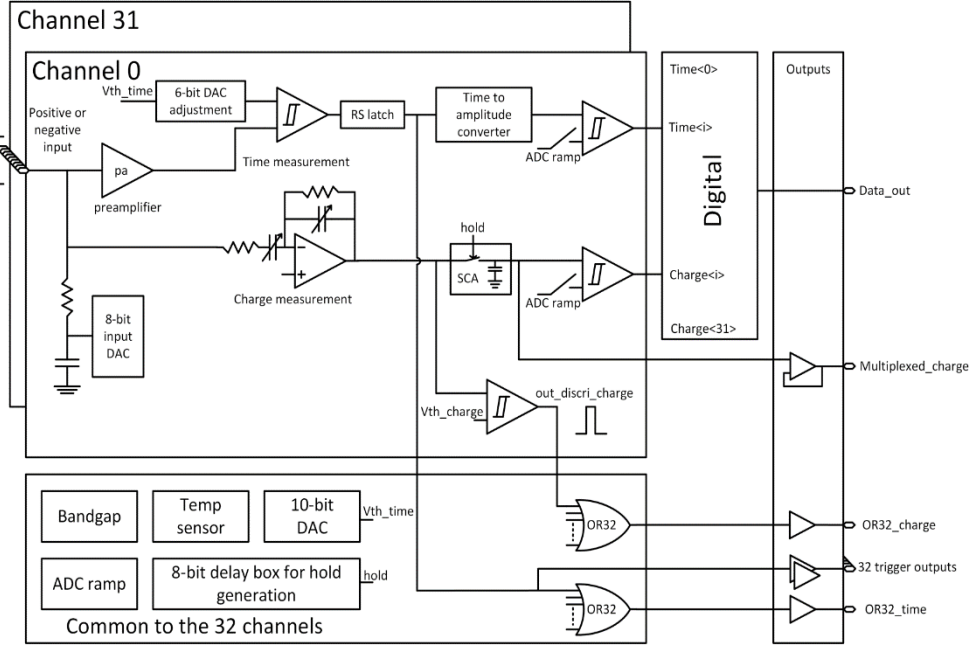
- 32 channels (negative input)

- 32 trigger outputs
- NOR32_chaage
- NOR32 time
- Charge measurement over 10 bits
- Time measurement over 10 bits
- One multiplexed charge output

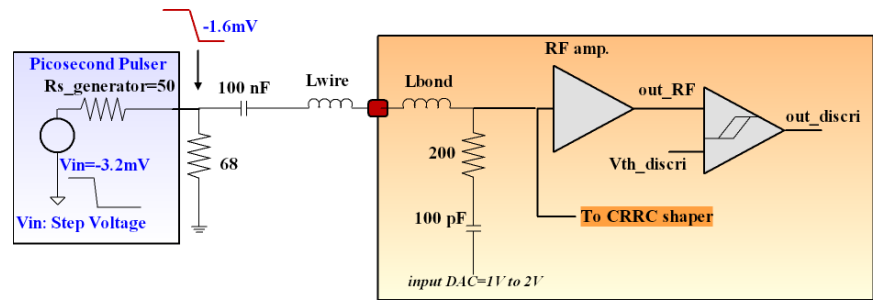
- Common trigger threshold adjustment and 6bit-dac/channel for individual adjustment

- 32 8bit-input dac for SiPM HV adjustment

- Power consumption 6 mW/ch

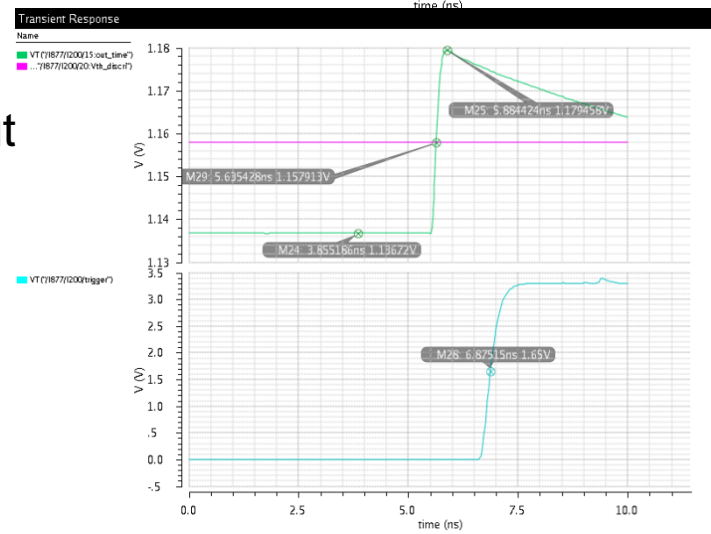
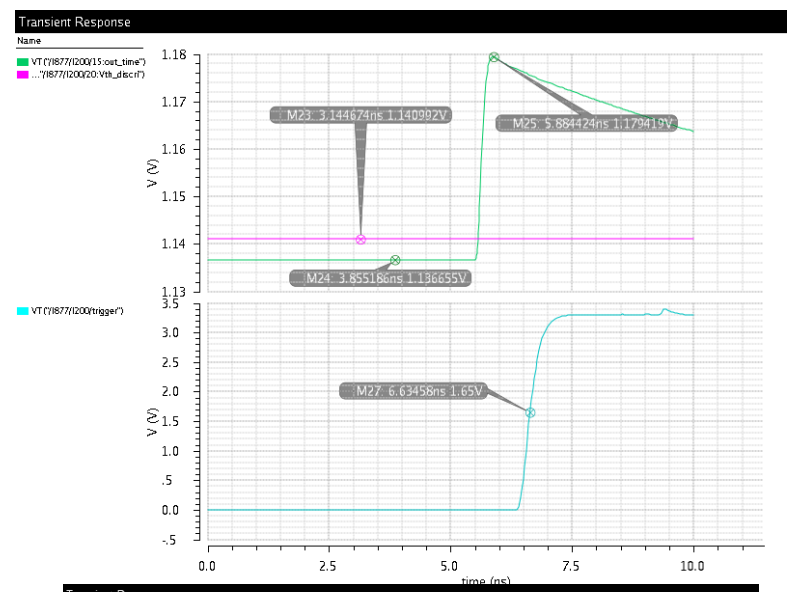


Parameter	Value
Detector Read-Out	SiPm
Number of Channels	32
Signal Polarity	negative
Sensitivity	voltage
Timing Resolution	< 75 ps
Dynamic Range	160 fC up to 400pC
Packaging & Dimension	TQFP 208 (28x28x1.4 mm), die : 4.7mmx4.3mm
Power Consumption	6 mW/channel
Inputs	32
Outputs	32 trigger outputs NOR32_chrage NOR32 time Charge measurement over 10 bits Time measurement over 10 bits One multiplexed charge output One multiplexed trigger output
Internal Programmable Features	Common trigger threshold adjustment and 6bit-dac/channel for individual adjustment Shaping time of the charge shaper 32 8bit-input dac for SiPM HV adjustment



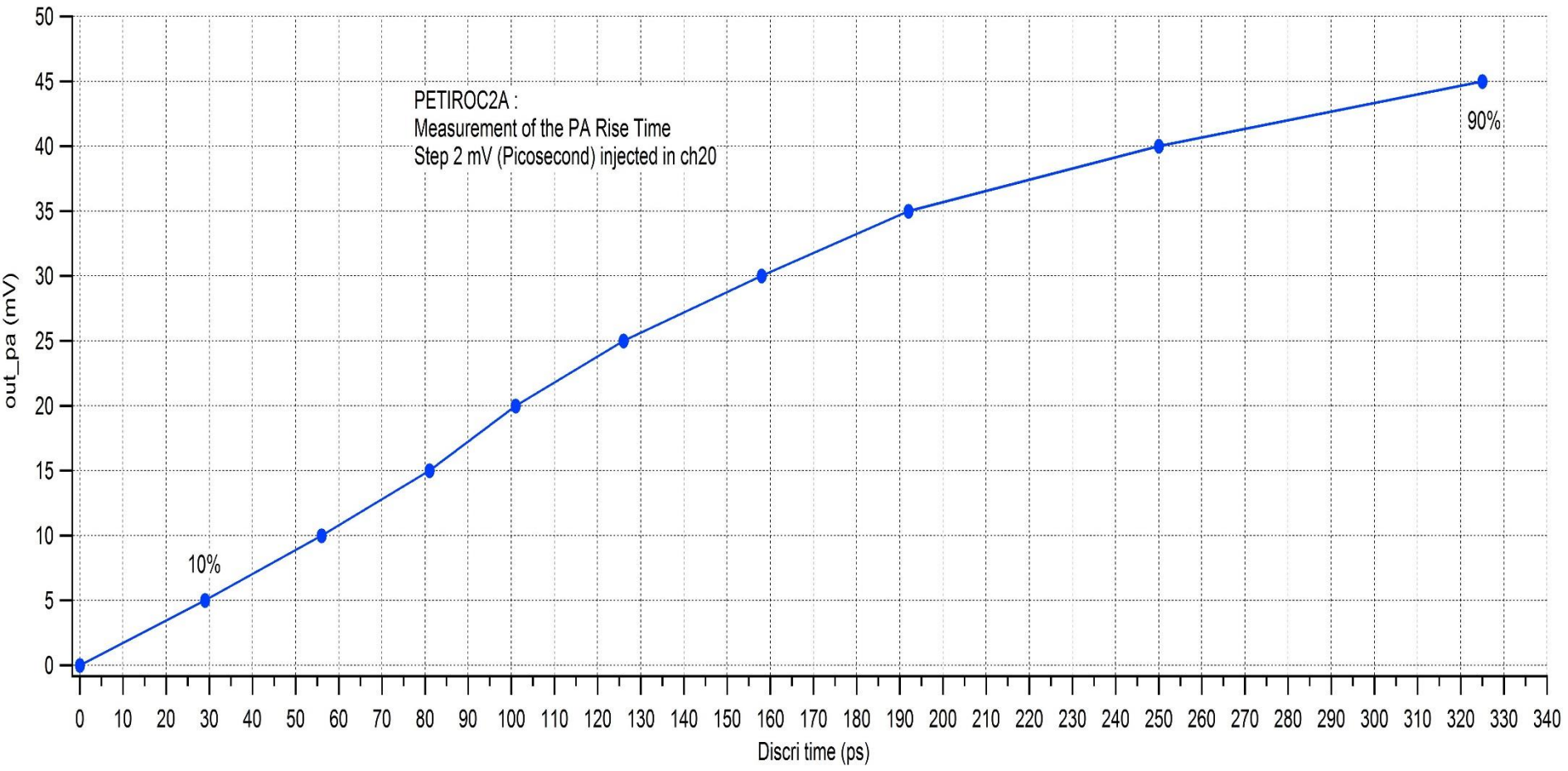
- Injection of a step
 - ⇒ $out_RF = E0(1-e^{-t/\tau})$
 - ⇒ $BW = 0.1 / \Delta t_{10\%-50\%}$
 - Simul of PA alone : BW= 6 GHz
 - Indirect measurement at discri output
 - Threshold set at 10 and 50% of the pa output

- Measurement:
 - BW of PA+discri > 1GHz**
 - ⇒ tr (amplifier) < 300ps**

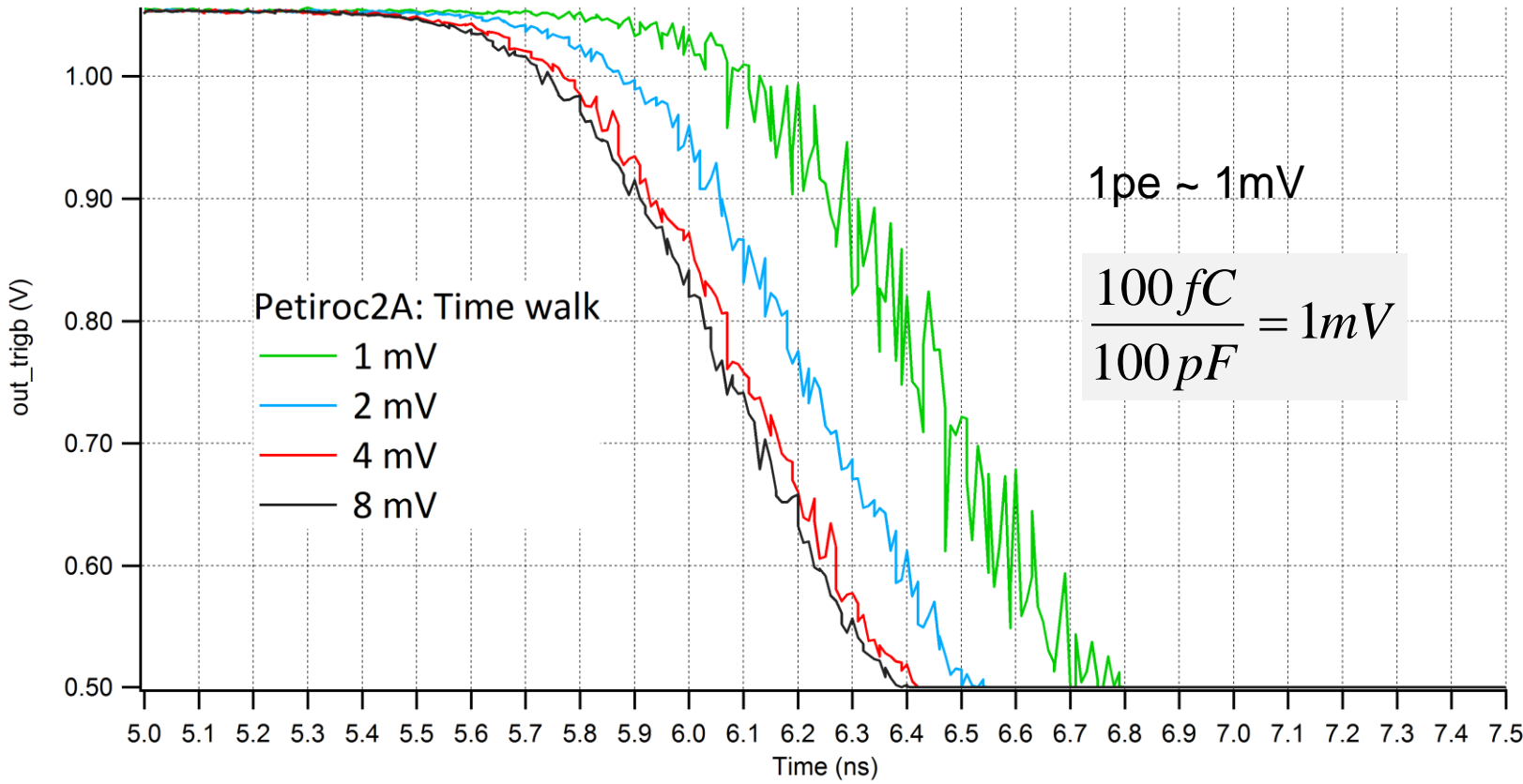


PETIROC2A: PA+DISCRI Rise Time measurement

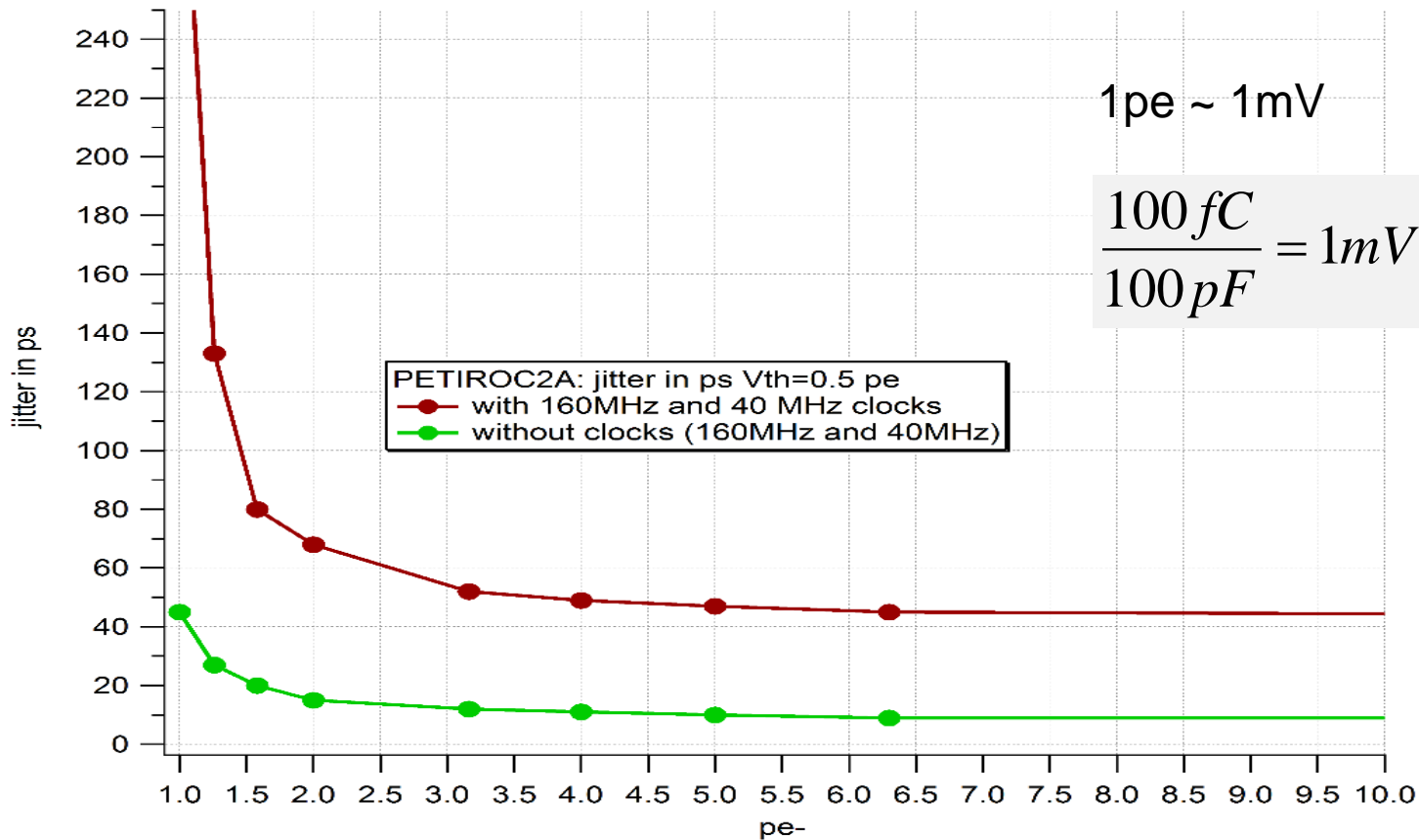
- t_r 10%-90% = 300 ps



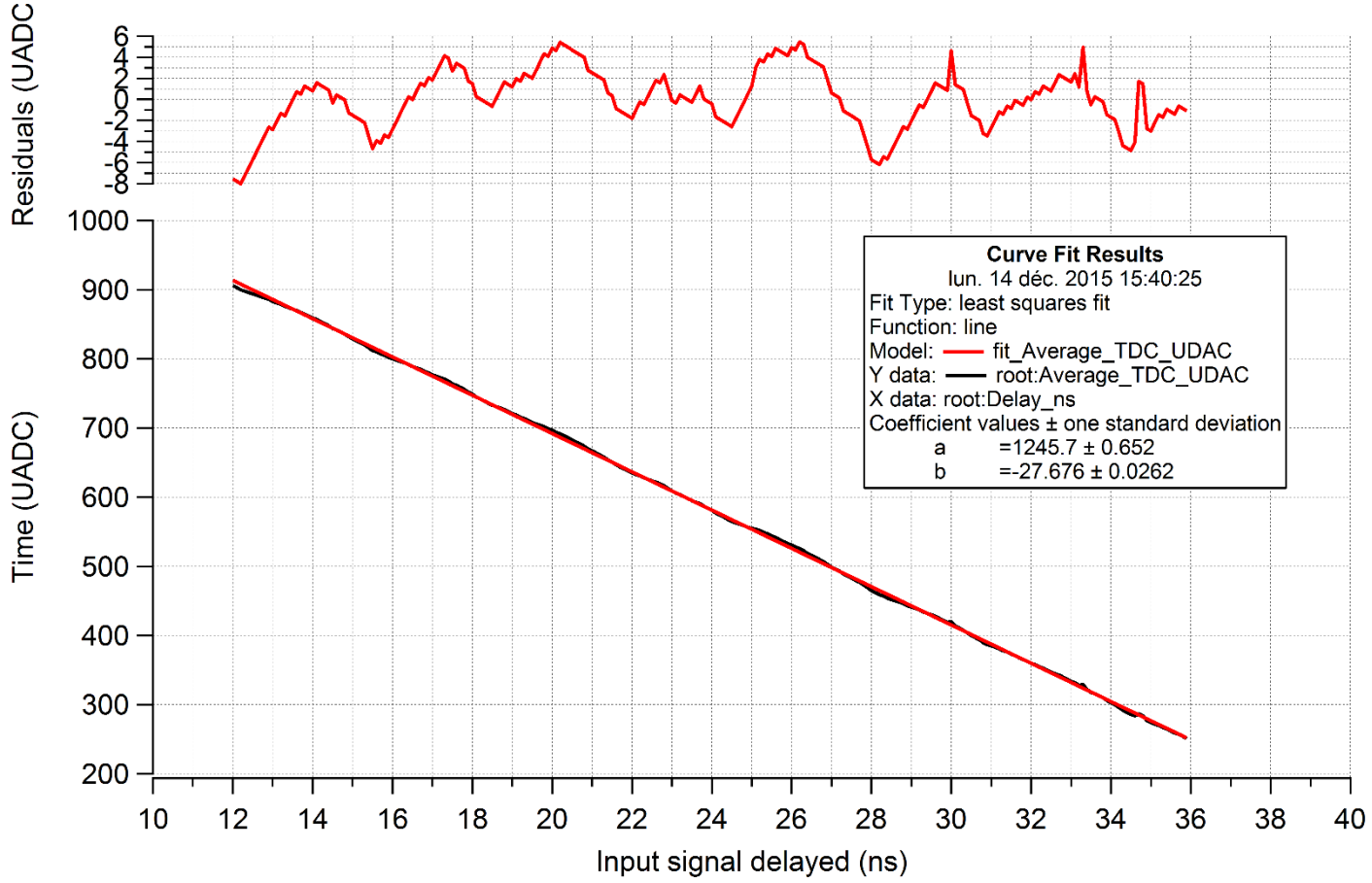
- Time walk < 350ps



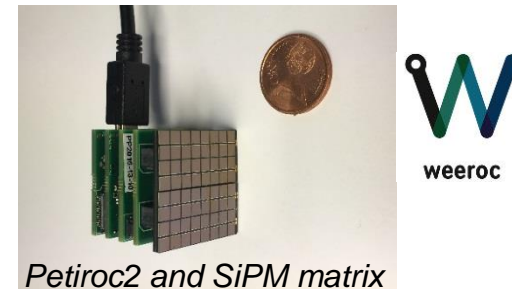
- Jitter vs threshold & injection, Jitter improves with signal
- Clock couplings: through substrate, better results expected with technologies that offer triple well trans (TSMC 130nm)
- jitter < 40 ps for injected charge > 1pe (= 1mV at the input)



- 160 MHz clock seen on the TDC (residuals).
 - rms of the histogram of the residuals: 2.6 ADC Unit
- ⇒ Time resolution: $2.6 \times 27 \text{ps (step)} = 70 \text{ ps rms}$



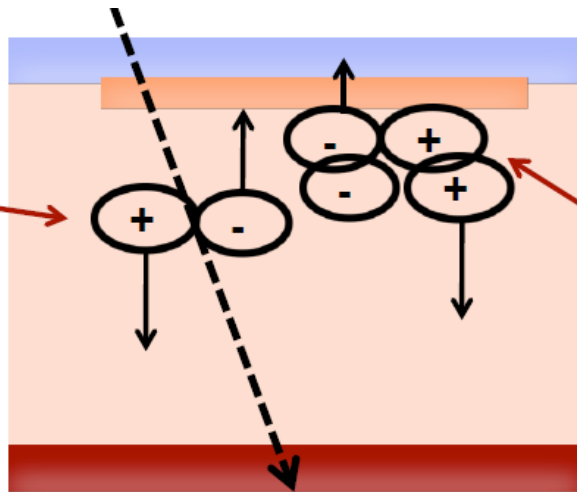
- Time resolution:
$$\sigma_t^2 = \left(\frac{t_{rise}}{S/N} \right)^2 + \left(\left[\frac{t_{rise} V_{th}}{S} \right]_{RMS} \right)^2 + \left(\frac{TDC_{bin}}{\sqrt{12}} \right)^2$$
 - jitter deeply dependent on the detector and time duration
 - Cd: must be as small as possible to have a large input signal: $V_{in} = Q_{in}/Cd$
 - ⇒ Try to optimize thickness and area of the sensor taking into account the radiation hardness and the **minimization of the drift time** (the larger the drift time, the larger the jitter)
 - Preamp bandwidth should match signal duration
 - Preamp transconductance gm determines noise, scaling as $\sqrt{I_d}$
 - +TW correction to be done: Time Over Threshold (TOT), Constant Fraction Discriminator (CFD)
 - TDC bin



- Time measurement: TAC or DLL
 - Petiroc2: TAC time resolution <100ps
 - Petiroc2 can be used either in full digital mode using the internal ADC and TDC or in analogue mode using the 32 trigger outputs and the multiplexed charge output. The analogue mode enables the use of external TDC
- Submission of blocks in TSMC130nm in May 2016: preamps, discris, TOT for CMS and ATLAS

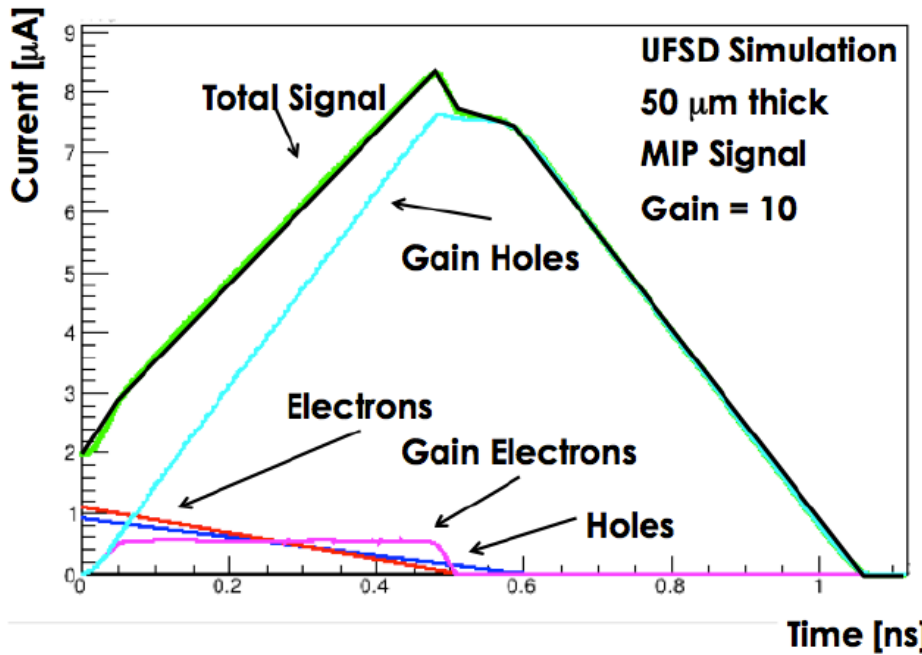
LGAD SIGNAL

Initial electron, holes



Gain electron:
absorbed immediately

Gain holes:
long drift home



- Electrons multiply and produce additional electrons and holes.
- Gain electrons have almost no effect
 - Gain holes dominate the signal
- ➔ No holes multiplications

CE in TSMC 130 nm: jitter vs tr (BW) and td

- Simulations for Cd=2pF and 20pF

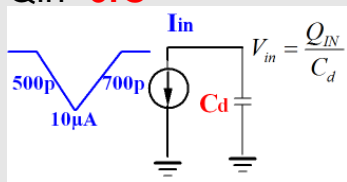
$$\sigma_t^J = \frac{\sigma_N}{dV} = \frac{t_r}{S} = \frac{\sqrt{t_{r_ampli}^2 + t_d^2}}{\frac{S}{N}}$$

- **Normalization made with LGAD pulse shape and 1 MIP = 6fC**

- 20pF → 2pF: Signal=Qin/Cd x 10 and I/10 => √gm divided by √10 => S/N x √10

$$\frac{S}{N} \approx \frac{\alpha \sqrt{g_m}}{C_d \sqrt{BW}} \approx \alpha \frac{\sqrt{g_m} \sqrt{t_{r_ampli}}}{C_d}$$

POWER: 0.5mW/ mm2

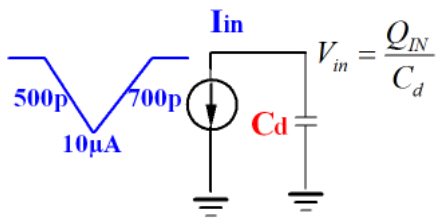
CE	Cd=2pF (Id=220 μA)	Cd=20pF (Id=2.1 mA)
<p>tr=500ps tf=700ps Qin=6fC</p> 	<p>out_fol = 36.6 mV tr_fol=700 ps BWa=1.1 GHz rms=0.485 mV S/N=75 σj=700ps/75=10 ps</p>	<p>out_fol=19 mV tr_fol=708ps BWa=1.2 GHz rms=1.18 mV S/N=16 σj=708ps/16=44 ps</p>
<p>tr_ampli=td CL=100fF Qin=6fC</p>	<p>out_fol=35.7 mV tr=1.1 ns BWa=410 MHz rms=0.39 mV S/N=92 σj=1.1ns/92=12 ps</p>	<p>out_fol=18.7 mV tr_fol=1.05 ns BWa=440 MHz rms=0.8 mV S/N=23.4 σj=1.05ns/23.4=45 ps</p>

Iin LGAD: WFM with 2 and 20pF

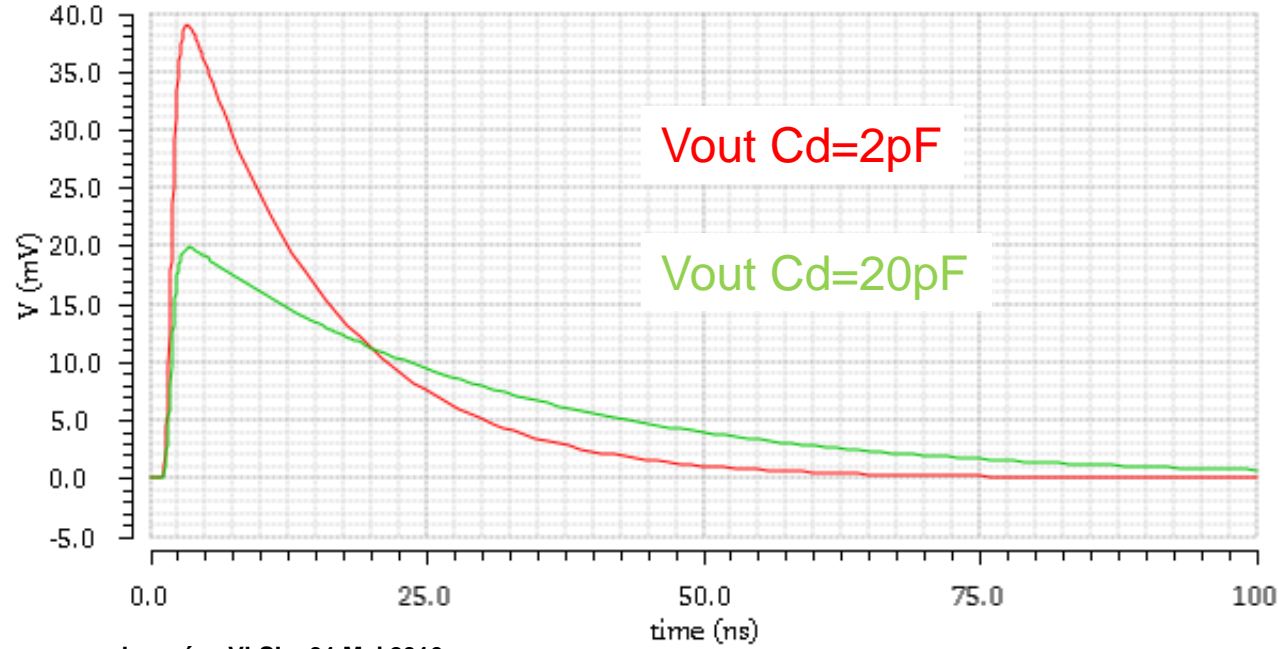
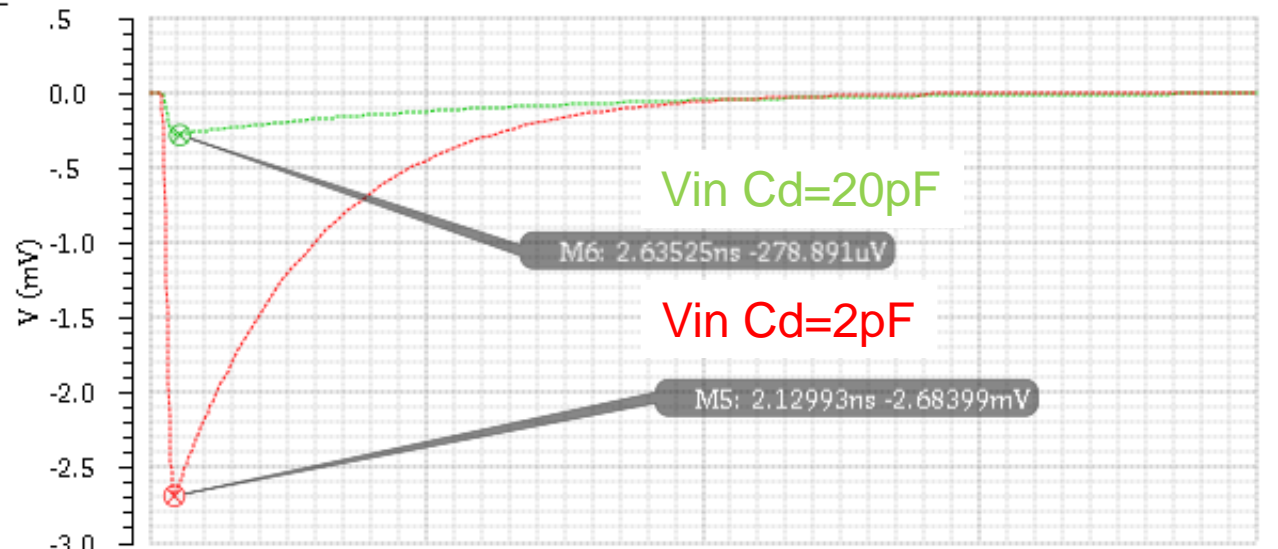
Transient Response

Name

- In with LGAD 6fC 2pF
- in Cd=20pF



- out with LGAD 6 fC 2pF
- out with LGAD Cd=20pF



20pF → 2pF:
 Signal=Qin/Cd x 10
 1/10 => √gm divided by √10